NOTICE OF REVISION (NOR)

THIS REVISION DESCRIBED BELOW HAS BEEN AUTHORIZED FOR THE DOCUMENT LISTED.

1. DATE (YYMMDD)	Form Approved OMB No. 0704-0188
97-01-27	

2. PROCURING ACTIVITY NO.	
3. DODAAC	

4. ORIGINATOR	b. ADDRESS *(Street, City, State, Zip Code)*	5. CAGE CODE	6. NOR NO.
a. TYPED NAME *(First, Middle Initial, Last)*	Defense Supply Center Columbus 3990 East Broad Street Columbus, OH 43216-5000	7. CAGE CODE 67268	8. DOCUMENT NO. 5962-97510
		67268	5962-R192-97

9. TITLE OF DOCUMENT	10. REVISION LETTER		11. ECP NO.
MICROCIRCUIT, LINEAR, WIDE INPUT VOLTAGE, DUAL OPERATIONAL AMPLIFIER, MONOLITHIC SILICON	a. CURRENT	b. NEW A	No users listed.

12. CONFIGURATION ITEM (OR SYSTEM) TO WHICH ECP APPLIES
All

13. DESCRIPTION OF REVISION

Sheet 1: Revisions ltr column; add "A".
Revisions description column; add "Changes in accordance with NOR 5962-R192-97".
Revisions date column; add "97-01-27".
Revision level block; add "A".
Rev status of sheets; for sheet 1 and 6, add "A".

Sheet 6: TABLE I. Common-mode rejection ratio test.
Under the conditions column, delete "V_{IC} = 0 V to 2.5 V" and substitute "$V_{IC} = V_{ICR}$ min".
Under the conditions column, delete "V_{IC} = 0 V to 4.5 V" and substitute "$V_{IC} = V_{ICR}$ min".
Revision level block; add "A".

14. THIS SECTION FOR GOVERNMENT USE ONLY

a. *(X one)*		
	X	(1) Existing document supplemented by the NOR may be used in manufacture.
		(2) Revised document must be received before manufacturer may incorporate this change.
		(3) Custodian of master document shall make above revision and furnish revised document.

b. ACTIVITY AUTHORIZED TO APPROVE CHANGE FOR GOVERNMENT	c. TYPED NAME *(First, Middle Initial, Last)*
DSCC-VAS	RAYMOND MONNIN

d. TITLE	e. SIGNATURE	f. DATE SIGNED (YYMMDD)
Chief, Microelectronics Team	RAYMOND MONNIN	97-01-27

15a. ACTIVITY ACCOMPLISHING REVISION	b. REVISION COMPLETED *(Signature)*	c. DATE SIGNED (YYMMDD)
DSCC-VAS	RICK OFFICER	97-01-27

DD Form 1695, APR 92 Previous editions are obsolete.

9004708 0027529 279

REVISIONS			
LTR	DESCRIPTION	DATE (YR-MO-DA)	APPROVED

REV																				
SHEET																				
REV																				
SHEET																				
REV STATUS OF SHEETS	REV																			
	SHEET	1	2	3	4	5	6	7	8	9	10									

PMIC N/A

STANDARD MICROCIRCUIT DRAWING

THIS DRAWING IS AVAILABLE FOR USE BY ALL DEPARTMENTS AND AGENCIES OF THE DEPARTMENT OF DEFENSE

AMSC N/A

PREPARED BY
RICK OFFICER

CHECKED BY
RAJESH PITHADIA

APPROVED BY
RAYMOND MONNIN

DRAWING APPROVAL DATE
96-12-31

REVISION LEVEL

DEFENSE SUPPLY CENTER COLUMBUS
COLUMBUS, OHIO 43216

MICROCIRCUIT, LINEAR, WIDE INPUT VOLTAGE, DUAL OPERATIONAL AMPLIFIER, MONOLITHIC SILICON

SIZE	CAGE CODE	
A	67268	5962-97510

SHEET 1 OF 10

9004708 0027530 T90

DESC FORM 193
JUL 94

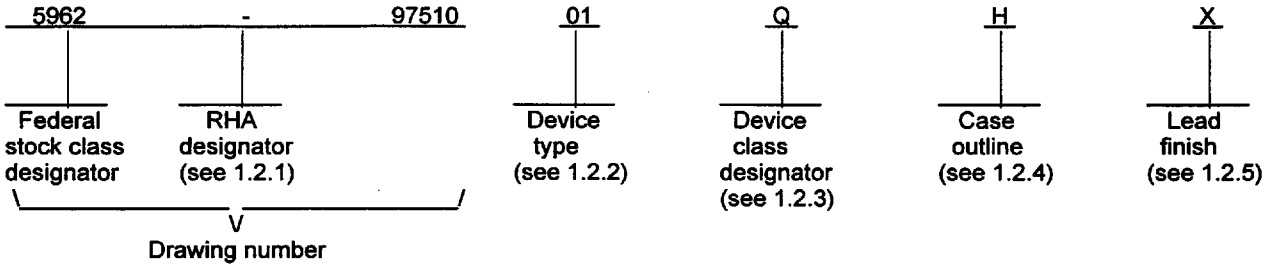
5962-E061-97

DISTRIBUTION STATEMENT A. Approved for public release; distribution is unlimited.

1. SCOPE

1.1 Scope. This drawing documents two product assurance class levels consisting of high reliability (device classes Q and M) and space application (device class V). A choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). When available, a choice of Radiation Hardness Assurance (RHA) levels are reflected in the PIN.

1.2 PIN. The PIN is as shown in the following example:



1.2.1 RHA designator. Device classes Q and V RHA marked devices meet the MIL-PRF-38535 specified RHA levels and are marked with the appropriate RHA designator. Device class M RHA marked devices meet the MIL-PRF-38535, appendix A specified RHA levels and are marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.

1.2.2 Device type(s). The device type(s) identify the circuit function as follows:

Device type	Generic number	Circuit function
01	TLV2432M	Rail-to-rail wide-input-voltage dual operational amplifiers
02	TLV2432AM	Rail-to-rail wide-input-voltage dual operational amplifiers (enhanced V_{IO})

1.2.3 Device class designator. The device class designator is a single letter identifying the product assurance level as follows:

Device class	Device requirements documentation
M	Vendor self-certification to the requirements for MIL-STD-883 compliant, non-JAN class level B microcircuits in accordance with MIL-PRF-38535, appendix A
Q or V	Certification and qualification to MIL-PRF-38535

1.2.4 Case outline(s). The case outline(s) are as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	Terminals	Package style
H	GDFP1-F10 or CDFP2-F10	10	Flat pack
P	GDIP1-T8 or CDIP2-T8	8	Dual-in-line
2	CQCC1-N20	20	Square leadless chip carrier

1.2.5 Lead finish. The lead finish is as specified in MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

1.3 Absolute maximum ratings. 1/

Supply voltage (V_{DD})	+12.0 V dc 2/
Differential input voltage (V_{ID})	$\pm V_{DD}$ 3/
Input current, each input (I_{IN})	±5.0 mA
Output current (I_{OUT})	±50.0 mA
Total current into $+V_{DD}$	±50.0 mA
Total current out of $-V_{DD}$	±50.0 mA
Duration of short-circuit current at (or below) +25°C	Unlimited 4/
Continuous total power dissipation (P_D) 5/	
Case H	675 mW
Case P	1050 mW
Case 2	1375 mW
Operating free-air temperature range (T_A)	-55°C to +125°C
Storage temperature range (T_{STG})	-65°C to +150°C
Lead temperature 1.6 mm (1/16 seconds) from case for 10 seconds	+260°C
Maximum junction temperature (T_J)	+150°C
Thermal resistance, junction-to-case (Θ_{JC})	See MIL-STD-1835

1.4 Recommended operating conditions.

Supply voltage ($\pm V_{DD}$)	2.7 V dc to 10.0 V dc
Input voltage range (V_{IN})	$-V_{DD}$ to $+V_{DD}$ - 1.3 V
Common-mode input voltage (V_{IC})	$-V_{DD}$ to $+V_{DD}$ - 1.3 V
Case operating temperature range (T_A)	-55°C to +125°C

2. APPLICABLE DOCUMENTS

2.1 Government specification, standards, and handbooks. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those listed in the issue of the Department of Defense Index of Specifications and Standards (DoDISS) and supplement thereto, cited in the solicitation.

SPECIFICATION

MILITARY

MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for.

STANDARDS

MILITARY

MIL-STD-883 - Test Methods and Procedures for Microelectronics.
MIL-STD-973 - Configuration Management.
MIL-STD-1835 - Microcircuit Case Outlines.

1/ Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.
2/ All voltage values, except differential voltages, are with respect to the midpoint between $+V_{DD}$ and $-V_{DD}$.
3/ Differential voltages are at the noninverting input with respect to the inverting input. Excessive current flows if the input is brought below $-V_{DD}$ - 0.3 V.
4/ The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure that the maximum dissipation rating is not exceeded.
5/ Above T_A = +25°C, derate by the following factors; case H at 5.4 mW/°C, case P at 8.4 mW/°C, and case 2 at 11.0 mW/°C.

HANDBOOKS

MILITARY

MIL-HDBK-103 - List of Standard Microcircuit Drawings (SMD's).
MIL-HDBK-780 - Standard Microcircuit Drawings.

(Unless otherwise indicated, copies of the specification, standards, and handbooks are available from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.2 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 Item requirements. The individual item requirements for device classes Q and V shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. The individual item requirements for device class M shall be in accordance with MIL-PRF-38535, appendix A for non-JAN class level B devices and as specified herein.

3.2 Design, construction, and physical dimensions. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein for device classes Q and V or MIL-PRF-38535, appendix A and herein for device class M.

3.2.1 Case outline(s). The case outline(s) shall be in accordance with 1.2.4 herein.

3.2.2 Terminal connections. The terminal connections shall be as specified on figure 1.

3.2.3 Radiation exposure circuit. The radiation exposure circuit shall be as specified when available.

3.3 Electrical performance characteristics and postirradiation parameter limits. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full ambient operating temperature range.

3.4 Electrical test requirements. The electrical test requirements shall be the subgroups specified in table II. The electrical tests for each subgroup are defined in table I.

3.5 Marking. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked as listed in MIL-HDBK-103. For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device. For RHA product using this option, the RHA designator shall still be marked. Marking for device classes Q and V shall be in accordance with MIL-PRF-38535. Marking for device class M shall be in accordance with MIL-PRF-38535, appendix A.

3.5.1 Certification/compliance mark. The certification mark for device classes Q and V shall be a "QML" or "Q" as required in MIL-PRF-38535. The compliance mark for device class M shall be a "C" as required in MIL-PRF-38535, appendix A.

3.6 Certificate of compliance. For device classes Q and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.6.1 herein). For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-HDBK-103 (see 6.6.2 herein). The certificate of compliance submitted to DSCC-VA prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device classes Q and V, the requirements of MIL-PRF-38535 and herein or for device class M, the requirements of MIL-PRF-38535, appendix A and herein.

3.7 Certificate of conformance. A certificate of conformance as required for device classes Q and V in MIL-PRF-38535 or for device class M in MIL-PRF-38535, appendix A shall be provided with each lot of microcircuits delivered to this drawing.

TABLE I. Electrical performance characteristics.

Test	Symbol	Conditions 1/ $-55°C \le T_A \le +125°C$ unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
Input offset voltage	V_{IO}	V_{IC} = 0 V, $\pm V_{DD}$ = ±1.5 V V_O = 0 V, R_S = 50 Ω	1	01		2000	µV
			2, 3			2500	
			1	02		950	
			2, 3			2000	
		V_{IC} = 0 V, $\pm V_{DD}$ = ±2.5 V V_O = 0 V, R_S = 50 Ω	1	01		2000	
			2, 3			2500	
			1	02		950	
			2, 3			2000	
Input offset current	I_{IO}	V_{IC} = 0 V, $\pm V_{DD}$ = ±1.5 V V_O = 0 V, R_S = 50 Ω	2, 3	All		150	pA
		V_{IC} = 0 V, $\pm V_{DD}$ = ±2.5 V V_O = 0 V, R_S = 50 Ω	2, 3	All		150	
Input bias current	I_{IB}	V_{IC} = 0 V, $\pm V_{DD}$ = ±1.5 V V_O = 0 V, R_S = 50 Ω	2, 3	All		300	pA
		V_{IC} = 0 V, $\pm V_{DD}$ = ±2.5 V V_O = 0 V, R_S = 50 Ω	2, 3	All		300	
Common-mode input voltage range	V_{ICR}	$\lvert V_{IO}\rvert \le 5$ mV, R_S = 50 Ω, V_{DD} = 3.0 V	1	All	0 to 2.5		V
			2, 3		0 to 2.2		
		$\lvert V_{IO}\rvert \le 5$ mV, R_S = 50 Ω, V_{DD} = 5.0 V	1		0 to 4.5		
			2, 3		0 to 4.2		
High-level output voltage	V_{OH}	I_{OH} = -3 mA, V_{DD} = 3.0 V	2, 3	All	2.25		V
		I_{OH} = -5 mA, V_{DD} = 5.0 V	1, 2, 3		4.0		
Low-level output voltage	V_{OL}	V_{IC} = 0 V, I_{OL} = 3 mA, V_{DD} = 3.0 V	2,3	All		1.0	V
		V_{IC} = 2.5 V, I_{OL} = 5 mA, V_{DD} = 5.0 V				1.25	

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test	Symbol	Conditions 1/ $-55°C \le T_A \le +125°C$ unless otherwise specified	Group A subgroups	Device type	Limits		Unit
					Min	Max	
Large-signal differential voltage amplification	A_{VD}	V_{IC} = 1.5 V, 2/ V_{DD} = 3.0 V, R_L = 2 kΩ, V_O = 1 V to 2 V	4	All	1.5		V/mV
			5, 6		0.5		
		V_{IC} = 2.5 V, 3/ V_{DD} = 5.0 V, R_L = 2 kΩ, V_O = 1 V to 4 V	4		2.5		
			5, 6		0.5		
Common-mode rejection ratio	CMRR	V_{IC} = 0 V to 2.5 V, V_{DD} = 3.0 V V_O = 1.5 V, R_S = 50 Ω	1, 2, 3	All	70		dB
		V_{IC} = 0 V to 4.5 V, V_{DD} = 5.0 V V_O = 2.5 V, R_S = 50 Ω			70		
Supply-voltage rejection ratio ($\Delta V_{DD}/\Delta V_{IO}$)	k_{SVR}	V_{DD} = 2.7 V to 8 V, V_{DD} = 3.0 V, V_{IC} = V_{DD}/2, no load	1, 2, 3	All	80		dB
		V_{DD} = 4.4 V to 8 V, V_{DD} = 5.0 V, V_{IC} = V_{DD}/2, no load			80		
Supply current	I_{DD}	V_O = 1.5 V, no load, V_{DD} = 3.0 V	1	All		250	µA
			2, 3			260	
		V_O = 2.5 V, no load, V_{DD} = 5.0 V	1			250	
			2, 3			270	
Slew rate at unity gain	SR	V_{DD} = 3.0 V, 4/ R_L = 2 kΩ, C_L = 100 pF, V_O = 1.1 V to 1.9 V	4	All	0.15		V/µs
			5, 6		0.1		
		V_{DD} = 5.0 V, 5/ R_L = 2 kΩ, C_L = 100 pF, V_O = 1.5 V to 3.5 V	4		0.15		
			5, 6		0.1		

1/ All characteristics are measured with zero common-mode input voltages unless otherwise noted.

2/ Load resistance is referenced to 1.5 V.

3/ Load capacitance is referenced to 2.5 V.

4/ Load resistance and load capacitance are referenced to 1.5 V.

5/ Load resistance and load capacitance are referenced to 2.5 V.

Device type	01 and 02		
Case outlines	H	P	2
Terminal number	Terminal symbol		
1	NC	OUTPUT 1	NC
2	OUTPUT 1	-INPUT 1	OUTPUT 1
3	-INPUT 1	+INPUT 1	NC
4	+INPUT 1	$-V_{DD}$/GND	NC
5	$-V_{DD}$/GND	+INPUT 2	-INPUT 1
6	+INPUT 2	-INPUT 2	NC
7	-INPUT 2	OUTPUT 2	+INPUT 1
8	OUTPUT 2	$+V_{DD}$	NC
9	$+V_{DD}$	--	NC
10	NC	--	$-V_{DD}$/GND
11	--	--	NC
12	--	--	+INPUT 2
13	--	--	NC
14	--	--	NC
15	--	--	-INPUT 2
16	--	--	NC
17	--	--	OUTPUT 2
18	--	--	NC
19	--	--	NC
20	--	--	$+V_{DD}$

Pin description	
Terminal symbol	Description
+INPUT m (m = 1 to 2)	Non-inverting inputs
-INPUT m (m = 1 to 2)	Inverting inputs
OUTPUT m (m = 1 to 2)	Outputs

FIGURE 1. Terminal connections.

3.8 Notification of change for device class M. For device class M, notification to DSCC-VA of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change as defined in MIL-STD-973.

3.9 Verification and review for device class M. For device class M, DSCC, DSCC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.

3.10 Microcircuit group assignment for device class M. Device class M devices covered by this drawing shall be in microcircuit group number 73 (see MIL-PRF-38535, appendix A).

4. QUALITY ASSURANCE PROVISIONS

4.1 Sampling and inspection. For device classes Q and V, sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. For device class M, sampling and inspection procedures shall be in accordance with MIL-PRF-38535, appendix A.

4.2 Screening. For device classes Q and V, screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection.

4.2.1 Additional criteria for device class M.

a. Burn-in test, method 1015 of MIL-STD-883.

(1) Test condition B or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.

(2) T_A = +125°C, minimum.

b. Interim and final electrical test parameters shall be as specified in table II herein.

4.2.2 Additional criteria for device classes Q and V.

a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015 of MIL-STD-883.

b. Interim and final electrical test parameters shall be as specified in table II herein.

c. Additional screening for device class V beyond the requirements of device class Q shall be as specified in MIL-PRF-38535, appendix B.

4.3 Qualification inspection for device classes Q and V. Qualification inspection for device classes Q and V shall be in accordance with MIL-PRF-38535. Inspections to be performed shall be those specified in MIL-PRF-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

4.4 Conformance inspection. Technology conformance inspection for classes Q and V shall be in accordance with MIL-PRF-38535 including groups A, B, C, D, and E inspections and as specified herein except where option 2 of MIL-PRF-38535 permits alternate in-line control testing. Quality conformance inspection for device class M shall be in accordance with MIL-PRF-38535, appendix A and as specified herein. Inspections to be performed for device class M shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).

TABLE II. Electrical test requirements.

Test requirements	Subgroups (in accordance with MIL-STD-883, method 5005, table I)	Subgroups (in accordance with MIL-PRF-38535, table III)	
	Device class M	Device class Q	Device class V
Interim electrical parameters (see 4.2)	---	---	---
Final electrical parameters (see 4.2)	1,2,3,4 1/	1,2,3,4 1/	1,2,3,4 1/
Group A test requirements (see 4.4)	1,2,3,4,5,6	1,2,3,4,5,6	1,2,3,4,5,6
Group C end-point electrical parameters (see 4.4)	1	1	1
Group D end-point electrical parameters (see 4.4)	1	1	1
Group E end-point electrical parameters (see 4.4)	1,4	1,4	1,4

1/ PDA applies to subgroup 1 with the exception of input offset voltage (V_{IO}).

4.4.1 Group A inspection.

a. Tests shall be as specified in table II herein.

b. Subgroups 7, 8, 9, 10, and 11 in table I, method 5005 of MIL-STD-883 shall be omitted.

4.4.2 Group C inspection. The group C inspection end-point electrical parameters shall be as specified in table II herein.

4.4.2.1 Additional criteria for device class M. Steady-state life test conditions, method 1005 of MIL-STD-883:

a. Test condition B or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.

b. T_A = +125°C, minimum.

c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

4.4.2.2 Additional criteria for device classes Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.

4.4.3 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table II herein.

4.4.4 Group E inspection. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein).

a. End-point electrical parameters shall be as specified in table II herein.

b. For device classes Q and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535 for the RHA level being tested. For device class M, the devices shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535, appendix A for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table I at T_A = +25°C ±5°C, after exposure, to the subgroups specified in table II herein.

c. When specified in the purchase order or contract, a copy of the RHA delta limits shall be supplied.

5. PACKAGING

5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-PRF-38535 for device classes Q and V or MIL-PRF-38535, appendix A for device class M.

6. NOTES

6.1 Intended use. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.

6.1.1 Replaceability. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.

6.1.2 Substitutability. Device class Q devices will replace device class M devices.

6.2 Configuration control of SMD's. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished in accordance with MIL-STD-973 using DD Form 1692, Engineering Change Proposal.

6.3 Record of users. Military and industrial users should inform Defense Supply Center Columbus when a system application requires configuration control and which SMD's are applicable to that system. DSCC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DSCC-VA, telephone (614) 692-0525.

6.4 Comments. Comments on this drawing should be directed to DSCC-VA , Columbus, Ohio 43216-5000, or telephone (614) 692-0674.

6.5 Abbreviations, symbols, and definitions. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535 and MIL-HDBK-1331.

6.6 Sources of supply.

6.6.1 Sources of supply for device classes Q and V. Sources of supply for device classes Q and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DSCC-VA and have agreed to this drawing.

6.6.2 Approved sources of supply for device class M. Approved sources of supply for class M are listed in MIL-HDBK-103. The vendors listed in MIL-HDBK-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DSCC-VA.